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Kind regards,

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PDTC143ZMB



NPN resistor-equipped transistor; R1 = 4.7 k Ω , R2 = 47 k Ω Rev. 1 — 11 June 2012 Product data of

Product data sheet

1. **Product profile**

1.1 General description

NPN Resistor-Equipped Transistor (RET) in a leadless ultra small SOT883B Surface-Mounted Device (SMD) plastic package.

PNP complement: PDTA143ZMB.

1.2 Features and benefits

- 100 mA output current capability
- Reduces component count
- Built-in bias resistors
- Reduces pick and place costs
- Simplifies circuit design
- AEC-Q101 qualified
- Leadless ultra small SMD plastic package
- Low package height of 0.37 mm

1.3 Applications

- Low-current peripheral driver
- Control of IC inputs

- Replaces general-purpose transistors in digital applications
- Mobile applications

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
Io	output current		-	-	100	mA
R1	bias resistor 1 (input)	T _{amb} = 25 °C	3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		8	10	12	



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	I	input (base)		
2	G	GND (emitter)	1	十3
3	0	output (collector)	2 Transparent top view	1 R1 R2
			SOT883B (DFN1006B-3)	sym007

3. Ordering information

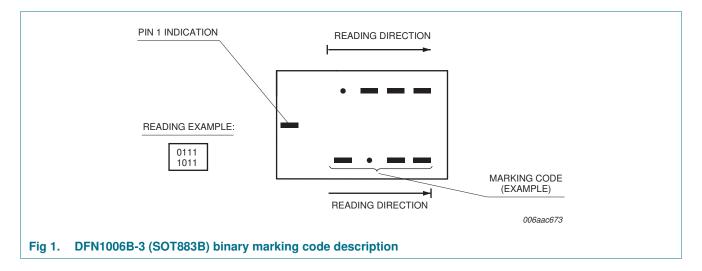
Table 3. Ordering information

Type number	number Package				
	Name	Description	Version		
PDTC143ZMB	DFN1006B-3	Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B		

4. Marking

Table 4. Marking codes

Type number	Marking code
PDTC143ZMB	0001 0110



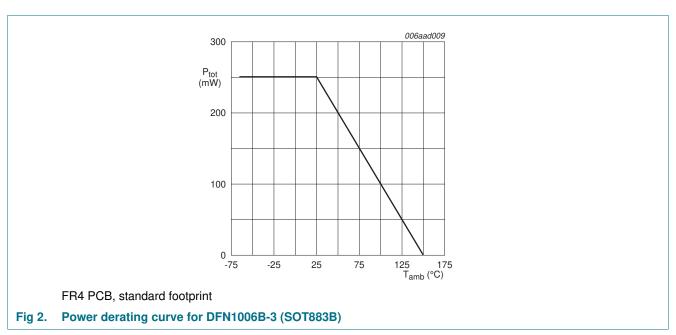
5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	50	V
V_{CEO}	collector-emitter voltage	open base		-	50	V
V_{EBO}	emitter-base voltage	open collector		-	5	V
V _I	input voltage	positive		-	30	V
		negative		-	-5	V
Io	output current			-	100	mA
I _{CM}	peak collector current	pulsed; t _p ≤ 1 ms		-	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	<u>[1]</u>	-	250	mW
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



6. Thermal characteristics

Table 6. Thermal characteristics

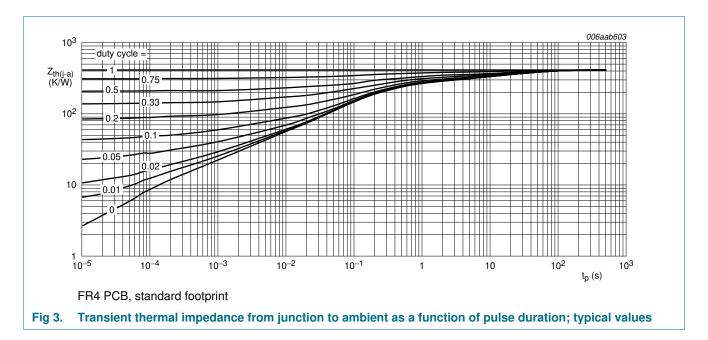
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	Ш	-	-	500	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

PDTC143ZMB

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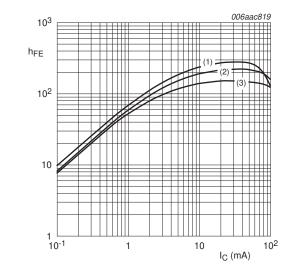


7. Characteristics

Table 7. Characteristics

Parameter	Conditions		Min	Тур	Max	Unit
collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	100	nA
	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	1	μΑ
current	$V_{CE} = 30 \text{ V}; I_B = 0 \text{ A}; T_j = 150 ^{\circ}\text{C}$		-	-	5	μΑ
emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	170	μΑ
DC current gain	V_{CE} = 5 V; I_{C} = 10 mA; T_{amb} = 25 °C		100	-	-	
collector-emitter saturation voltage	$I_C = 5 \text{ mA}; I_B = 0.25 \text{ mA}; T_{amb} = 25 \text{ °C}$		-	-	100	mV
off-state input voltage	V_{CE} = 5 V; I_{C} = 100 μ A; T_{amb} = 25 °C		-	0.6	0.5	V
on-state input voltage	V_{CE} = 0.3 V; I_{C} = 5 mA; T_{amb} = 25 °C		1.3	0.9	-	V
bias resistor 1 (input)	T _{amb} = 25 °C		3.3	4.7	6.1	kΩ
bias resistor ratio			8	10	12	
collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; T_{amb} = 25 \text{ °C}$		-	-	2.5	pF
transition frequency	$V_{CE} = 5 \text{ V; } I_{C} = 10 \text{ mA; } f = 100 \text{ MHz;}$ $T_{amb} = 25 \text{ °C}$	[1]	-	230	-	MHz
	collector-base cut-off current collector-emitter cut-off current emitter-base cut-off current DC current gain collector-emitter saturation voltage off-state input voltage on-state input voltage bias resistor 1 (input) bias resistor ratio collector capacitance	$ \begin{array}{c} \text{collector-base cut-off} \\ \text{current} \end{array} \hspace{0.5cm} V_{CB} = 50 \text{ V}; \ I_{E} = 0 \text{ A}; \ T_{amb} = 25 \text{ °C} \\ \text{current} \end{array} $ $ \begin{array}{c} \text{Collector-emitter cut-off} \\ \text{current} \end{array} \hspace{0.5cm} V_{CE} = 30 \text{ V}; \ I_{B} = 0 \text{ A}; \ T_{amb} = 25 \text{ °C} \\ \hline V_{CE} = 30 \text{ V}; \ I_{B} = 0 \text{ A}; \ T_{j} = 150 \text{ °C} \\ \hline V_{CE} = 30 \text{ V}; \ I_{D} = 0 \text{ A}; \ T_{j} = 150 \text{ °C} \\ \hline V_{CE} = 30 \text{ V}; \ I_{C} = 0 \text{ A}; \ T_{amb} = 25 \text{ °C} \\ \hline V_{CE} = 5 \text{ V}; \ I_{C} = 0 \text{ A}; \ T_{amb} = 25 \text{ °C} \\ \hline V_{CE} = 5 \text{ V}; \ I_{C} = 10 \text{ mA}; \ T_{amb} = 25 \text{ °C} \\ \hline V_{CE} = 5 \text{ V}; \ I_{C} = 100 \text{ µA}; \ T_{amb} = 25 \text{ °C} \\ \hline V_{CE} = 5 \text{ V}; \ I_{C} = 100 \text{ µA}; \ T_{amb} = 25 \text{ °C} \\ \hline V_{CE} = 0.3 \text{ V}; \ I_{C} = 5 \text{ mA}; \ T_{amb} = 25 \text{ °C} \\ \hline V_{CE} = 0.3 \text{ V}; \ I_{C} = 0 \text{ A}; \ I_{C} = 0 A$	$ \begin{array}{c} \text{collector-base cut-off} \\ \text{current} \end{array} \hspace{0.5cm} V_{CB} = 50 \text{ V}; \ I_{E} = 0 \text{ A}; \ T_{amb} = 25 \text{ °C} \\ \text{current} \end{array} $ $ \begin{array}{c} \text{Collector-emitter cut-off} \\ \text{current} \end{array} \hspace{0.5cm} V_{CE} = 30 \text{ V}; \ I_{B} = 0 \text{ A}; \ T_{amb} = 25 \text{ °C} \\ \hline V_{CE} = 30 \text{ V}; \ I_{B} = 0 \text{ A}; \ T_{j} = 150 \text{ °C} \\ \hline V_{CE} = 30 \text{ V}; \ I_{D} = 0 \text{ A}; \ T_{j} = 150 \text{ °C} \\ \hline V_{CE} = 30 \text{ V}; \ I_{C} = 0 \text{ A}; \ T_{amb} = 25 \text{ °C} \\ \hline V_{CE} = 5 \text{ V}; \ I_{C} = 0 \text{ A}; \ T_{amb} = 25 \text{ °C} \\ \hline V_{CE} = 5 \text{ V}; \ I_{C} = 10 \text{ mA}; \ T_{amb} = 25 \text{ °C} \\ \hline V_{CE} = 5 \text{ V}; \ I_{C} = 100 \text{ µA}; \ T_{amb} = 25 \text{ °C} \\ \hline V_{CE} = 5 \text{ V}; \ I_{C} = 100 \text{ µA}; \ T_{amb} = 25 \text{ °C} \\ \hline V_{CE} = 0.3 \text{ V}; \ I_{C} = 5 \text{ mA}; \ T_{amb} = 25 \text{ °C} \\ \hline V_{CE} = 0.3 \text{ V}; \ I_{C} = 0 \text{ A}; \ I_{C} = 0 A$	$ \begin{array}{c} \text{collector-base cut-off} \\ \text{current} \end{array} \hspace{0.5cm} V_{CB} = 50 \text{ V}; \ I_{E} = 0 \text{ A}; \ T_{amb} = 25 \text{ °C} \\ \text{current} \end{array} \hspace{0.5cm} - \\ \begin{array}{c} \text{collector-emitter cut-off} \\ \text{current} \end{array} \hspace{0.5cm} V_{CE} = 30 \text{ V}; \ I_{B} = 0 \text{ A}; \ T_{amb} = 25 \text{ °C} \\ \hline V_{CE} = 30 \text{ V}; \ I_{B} = 0 \text{ A}; \ T_{j} = 150 \text{ °C} \\ \end{array} \hspace{0.5cm} - \\ \begin{array}{c} \text{emitter-base cut-off} \\ \text{current} \end{array} \hspace{0.5cm} V_{EB} = 5 \text{ V}; \ I_{C} = 0 \text{ A}; \ T_{amb} = 25 \text{ °C} \\ \end{array} \hspace{0.5cm} - \\ \\ \begin{array}{c} \text{DC current gain} \\ \text{Collector-emitter} \\ \text{IC} = 5 \text{ W}; \ I_{C} = 10 \text{ mA}; \ T_{amb} = 25 \text{ °C} \\ \end{array} \hspace{0.5cm} - \\ \\ \begin{array}{c} \text{collector-emitter} \\ \text{saturation voltage} \\ \text{off-state input voltage} \end{array} \hspace{0.5cm} V_{CE} = 5 \text{ V}; \ I_{C} = 100 \text{ μA}; \ T_{amb} = 25 \text{ °C} \\ \end{array} \hspace{0.5cm} - \\ \\ \begin{array}{c} \text{on-state input voltage} \\ \text{Voltage} \end{array} \hspace{0.5cm} V_{CE} = 5 \text{ V}; \ I_{C} = 5 \text{ mA}; \ T_{amb} = 25 \text{ °C} \\ \end{array} \hspace{0.5cm} 1.3 \\ \\ \begin{array}{c} \text{bias resistor 1 (input)} \\ \text{Subside resistor ratio} \end{array} \hspace{0.5cm} T_{amb} = 25 \text{ °C} \\ \\ \begin{array}{c} \text{Collector capacitance} \\ \text{Collector capacitance} \end{array} \hspace{0.5cm} V_{CB} = 10 \text{ V}; \ I_{C} = 10 \text{ mA}; \ I_{E} = 0 \text{ A}; $	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$

^[1] Characteristics of built-in transistor.



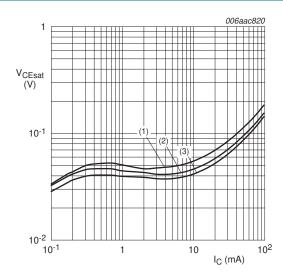
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 4. DC current gain as a function of collector current; typical values



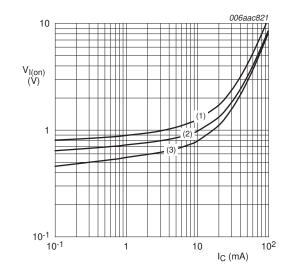
$$I_C/I_B = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 5. Collector-emitter saturation voltage as a function of collector current; typical values



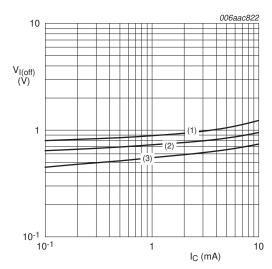
$$V_{CE} = 0.3 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 6. On-state input voltage as a function of collector current; typical values



$$V_{CE} = 5 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 7. Off-state input voltage as a function of collector current; typical values

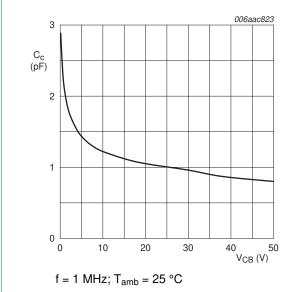


Fig 8. Collector capacitance as a function of collector-base voltage; typical values

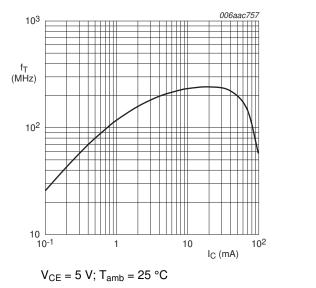


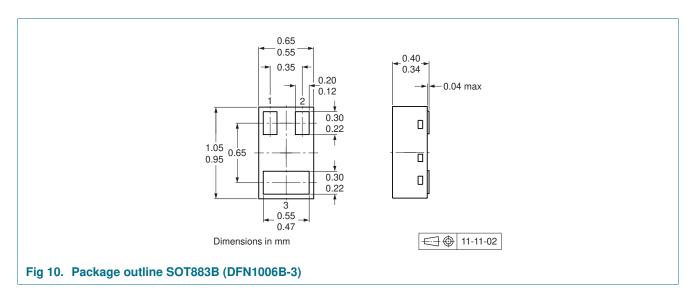
Fig 9. Transition frequency as a function of collector current; typical values of built-in transistor

8. Test information

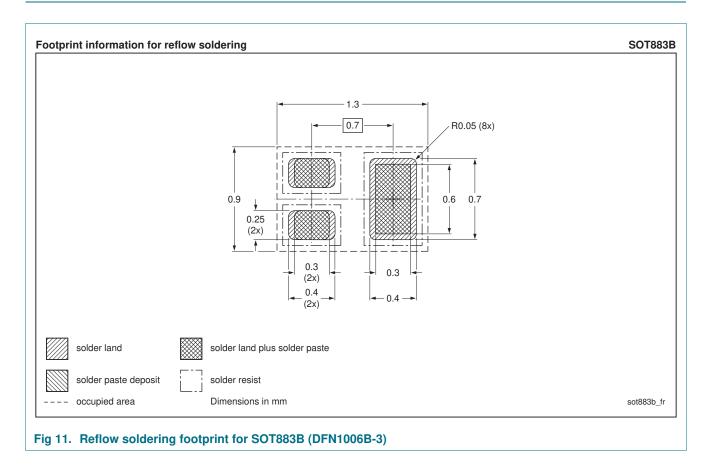
8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

9. Package outline



10. Soldering





11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PDTC143ZMB v.1	20120611	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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PDTC143ZMB

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For sales office addresses, please send an email to:salesaddresses@nxp.com

PDTC143ZMB

NPN resistor-equipped transistor; R1 = 4.7 k Ω , R2 = 47 k Ω

14. Contents

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